

PMEG2010AEJ

20 V, 1 A very low V_F MEGA Schottky barrier rectifier in SOD323F package

Rev. 02 — 14 October 2005

Product data sheet



1. Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD323F (SC-90) very small and flat lead Surface Mounted Device (SMD) plastic package.

1.2 Features

Forward current: ≤ 1 AReverse voltage: ≤ 20 V

Very low forward voltage

Very small and flat lead SMD plastic package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Inverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 1: Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
l _F	forward current	T _{sp} ≤ 55 °C	-	-	1	Α
V_R	reverse voltage		-	-	20	V
V _F	forward voltage	$I_F = 1000 \text{ mA}$	<u>[1]</u> _	480	550	mV

[1] Pulse test: $t_0 \le 300 \,\mu\text{s}$; $\delta \le 0.02$.



2. Pinning information

Table 2: Pinning

Pin	Description	Simplified outline	Symbol
1	cathode	[1]	
2	anode	1 2	1
			sym001

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
PMEG2010AEJ	SC-90	plastic surface mounted package; 2 leads	SOD323F

4. Marking

Table 4: Marking codes

Type number	Marking code
PMEG2010AEJ	EM

5. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage		-	20	V
I _F	forward current	T _{sp} ≤ 55 °C	-	1	Α
I _{FRM}	repetitive peak forward current	$t_p \le 1$ ms; $\delta \le 0.25$	-	5.5	Α
I _{FSM}	non-repetitive peak forward current	square wave; $t_p = 8 \text{ ms}$	-	10	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	360	mW
			[2]	830	mW
Tj	junction temperature		-	150	°C
T_{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 6: Thermal characteristics

Symbol	Parameter	Conditions	Mir	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	350	K/W
			[1] [3]	-	150	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		<u>[4]</u> _	-	55	K/W

^[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and $I_{F(AV)}$ rating are available on request.

- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Solder point of cathode tab.

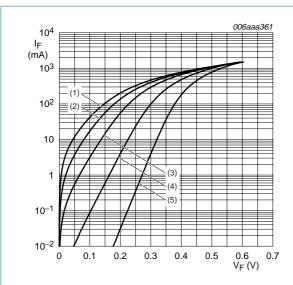
7. Characteristics

Table 7: Characteristics

T_{amb} = 25 °C unless otherwise specified.

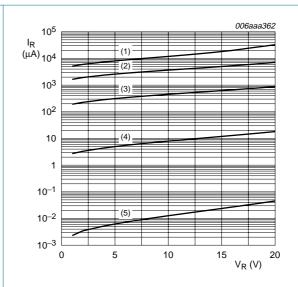
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage		<u>[1]</u>			
		I _F = 10 mA	-	240	270	mV
		I _F = 100 mA	-	300	350	mV
		$I_F = 500 \text{ mA}$	-	400	460	mV
		$I_F = 1000 \text{ mA}$	-	480	550	mV
I _R	reverse current	$V_R = 5 V$	-	5	10	μΑ
		V _R = 8 V	-	7	20	μΑ
		$V_R = 10 \text{ V}$	-	8	30	μΑ
		$V_R = 15 V$	-	10	50	μΑ
		V _R = 20 V	-	15	70	μΑ
C _d	diode capacitance	$V_R = 1 V$; $f = 1 MHz$	-	40	50	pF

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



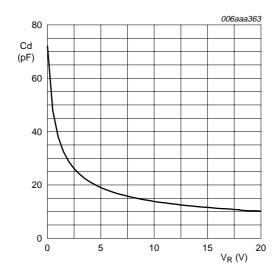
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \,^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Reverse current as a function of reverse voltage; typical values

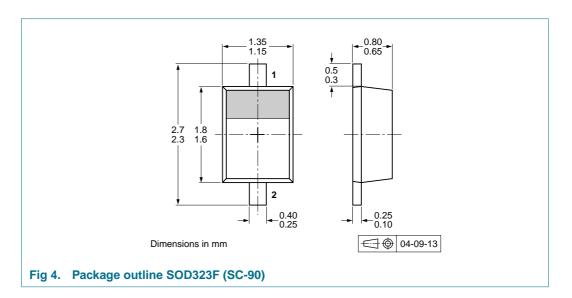


 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$

Fig 3. Diode capacitance as a function of reverse voltage; typical values

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8. Package outline



9. Packing information

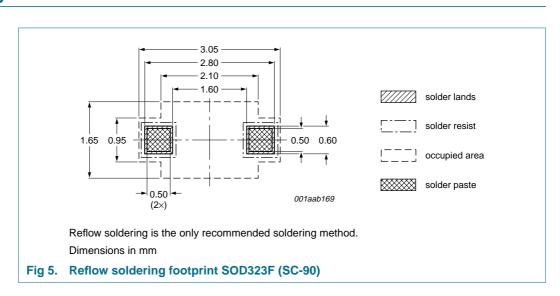
Table 8: Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing of	quantity
			3000	10000
PMEG2010AEJ	SOD323F	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see $\underline{\text{Section } 17}$.

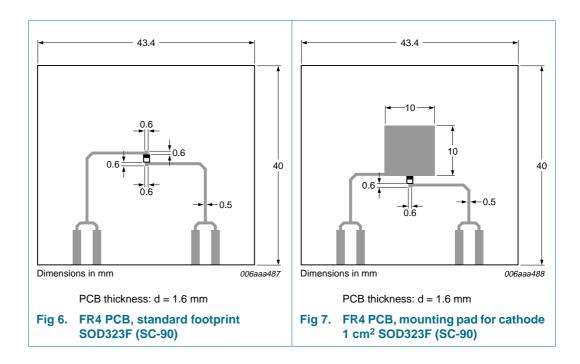
10. Soldering



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11. Mounting



12. Revision history

Table 9: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PMEG2010AEJ_2	20051014	Product data sheet	-	-	PMEG2010AEJ_1
Modifications:	 Section 1.3 Section 1.3 Table 5 "Li Table 6 "TI Table 6: Ta Figure 4 "F Table 8 "Pa Section 11 	1 "General description": 2 "Features": amended 3 "Applications": amende miting values": I _{FSM} non- miting values": typing er nermal characteristics": able note 4 added to R _{th} (Package outline SOD323 acking methods": table d "Mounting": added	ed -repetitive peak forw ror for value P _{tot} tota Table note 1 amend j-sp) thermal resistar BF (SC-90)": superso	al power dissipation ed ace from junction to eded by minimized	on amended a corrected a solder point
PMEG2010AEJ_1	20050302	Product data sheet	-	9397 750 14595	-

13. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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- [2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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